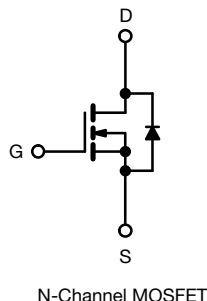
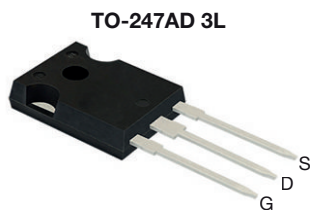


# MaxSiC™ 1200 V N-Channel SiC MOSFET



N-Channel MOSFET

**Marking Code:** 120A250FW

## PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	1200	
$R_{DS(on)}$ typ. (mΩ) at 25 °C	$V_{GS} = 20$ V	250
$Q_g$ typ. (nC)	20	
$I_D$ (A)	10.5	
$C_{oss}$ (pF)	21.2	
$P_D$ (W)	56	
Configuration	Single	

## ORDERING INFORMATION

Package	TO-247AD 3L
Lead (Pb)-free and halogen-free	MXP120A250FW-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage <sup>a</sup>		V <sub>DS</sub>	1200	V
Gate-source voltage		V <sub>GS</sub>	-10 / +22	
Recommended operation voltage of gate-source		V <sub>GSOP</sub>	-5 / +20	
Continuous drain current	T <sub>C</sub> = 25 °C	I <sub>D</sub>	10.5	A
	T <sub>C</sub> = 100 °C	I <sub>D</sub>	6.7	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	21	
Short-circuit withstand time <sup>c</sup>		T <sub>SC</sub>	3	μs
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	56	W
	T <sub>C</sub> = 100 °C	P <sub>D</sub>	22	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature)	For 10 s		260	°C

### Notes

- $T_J = 25$  °C to 150 °C
- Repetitive rating; pulse width limited by maximum junction temperature
- Verified by the design / characterization

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## FEATURES

- Fast switching speed
- Short circuit withstand time 3 μs
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

## APPLICATIONS

- Charger
- Industrial UPS
- Boost inverter
- DC/DC converter



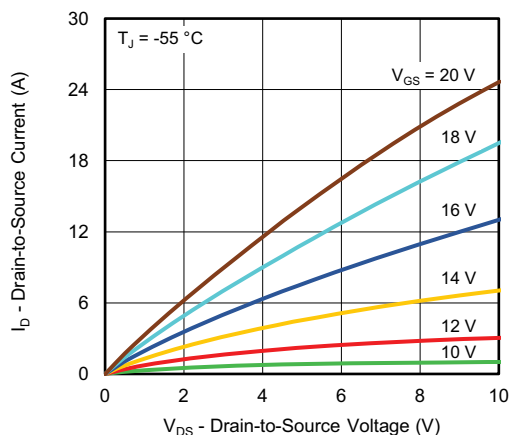
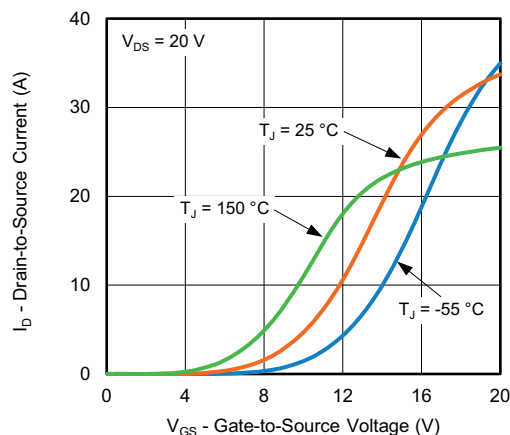
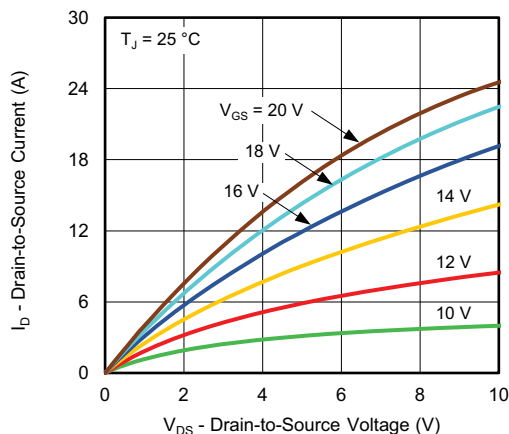
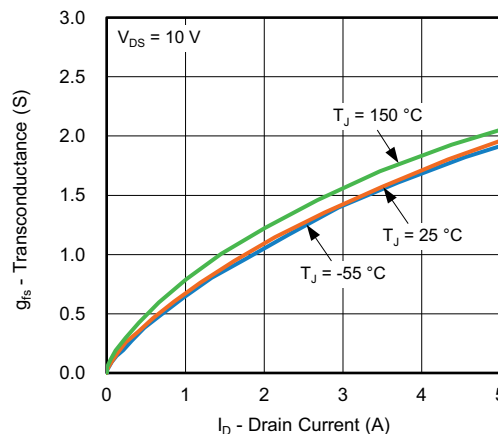
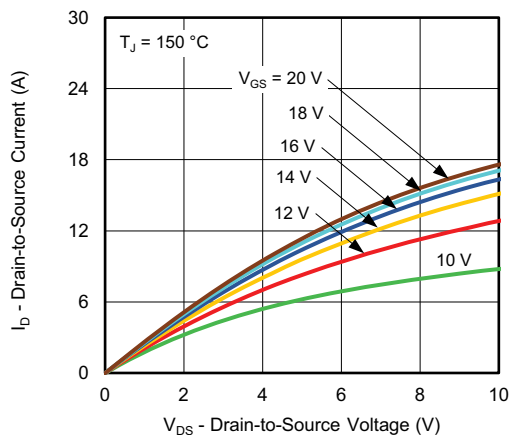
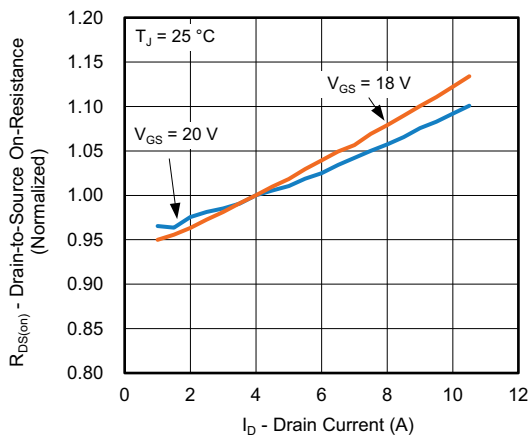
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

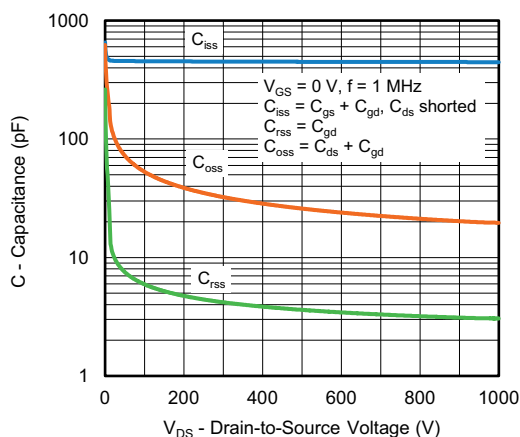
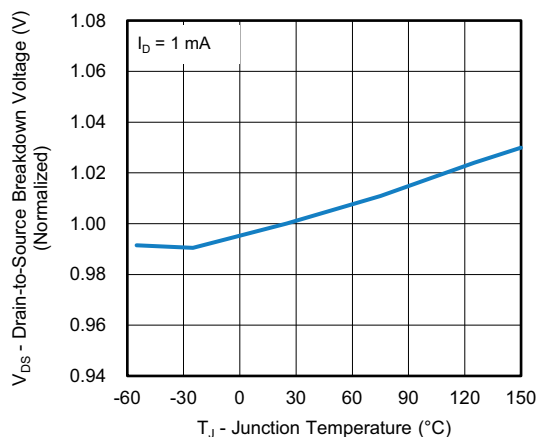
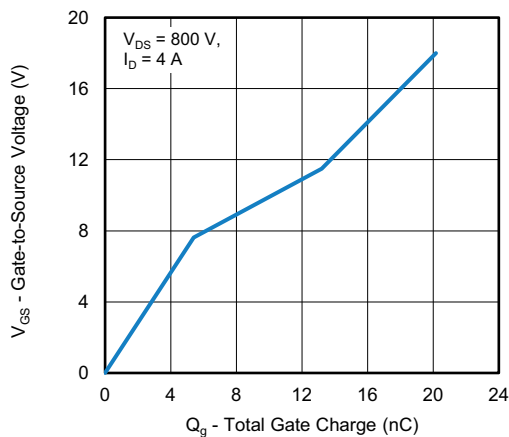
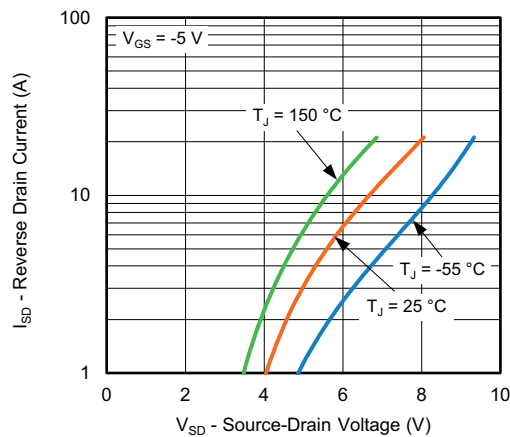
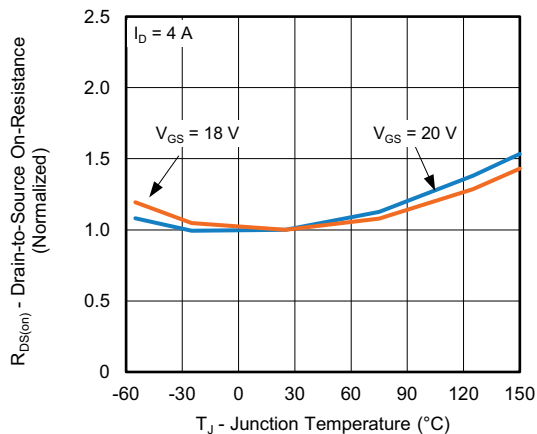
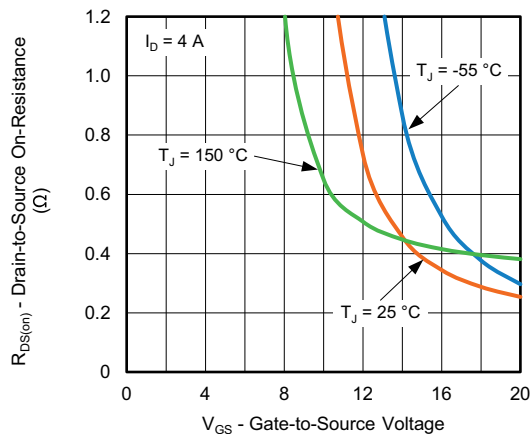
**THERMAL RESISTANCE RATINGS**

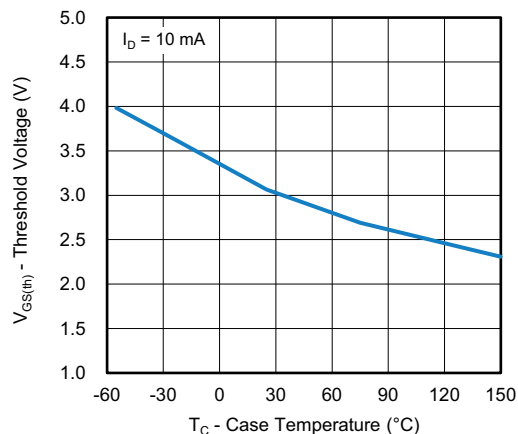
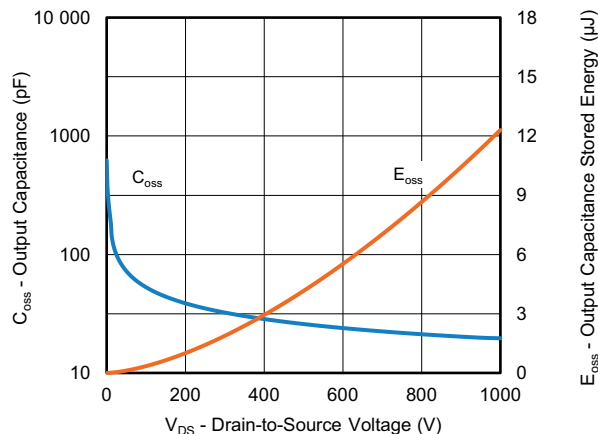
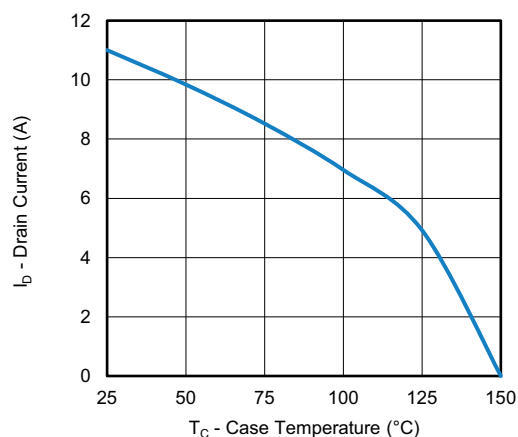
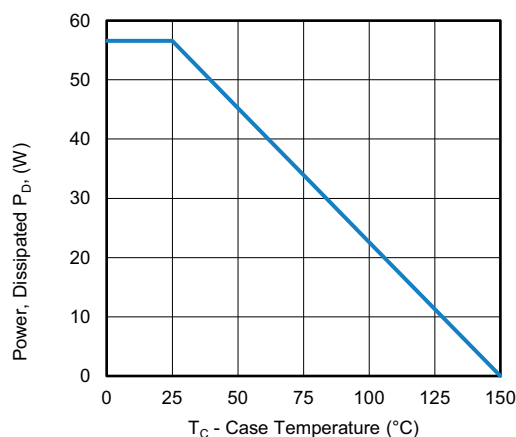
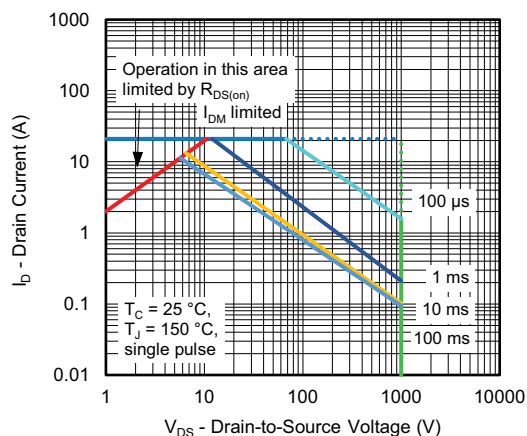
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	40	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	2.24	

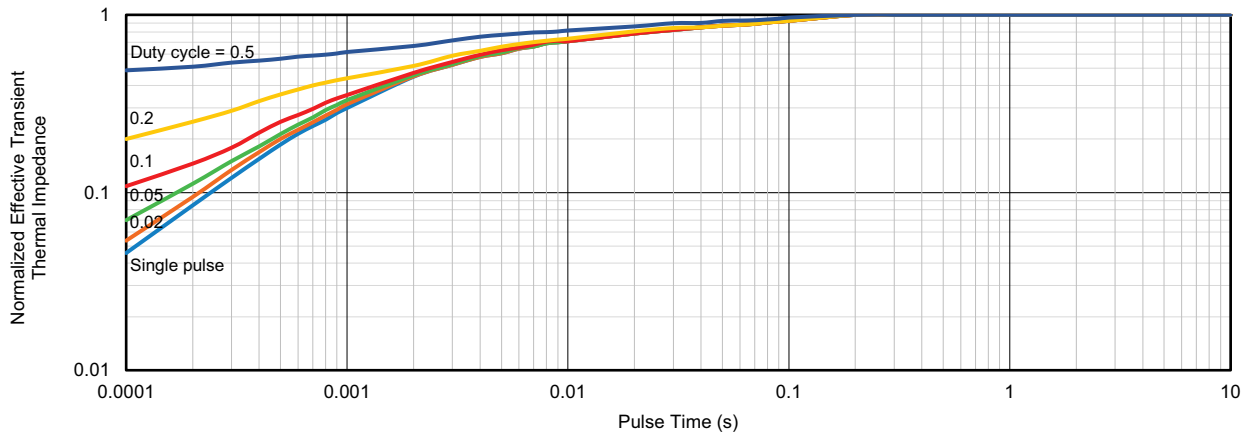
**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	1200	-	-	V
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 10 mA	-	3.1	-	V
		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 10 mA, T <sub>J</sub> = 150 °C	-	2.3	-	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = +22 V, V <sub>DS</sub> = 0 V	-	-	100	nA
		V <sub>GS</sub> = -10 V, V <sub>DS</sub> = 0 V	-	-	-100	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 960 V, V <sub>GS</sub> = 0 V	-	-	10	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 20 V, I <sub>D</sub> = 4 A	-	250	313	mΩ
		V <sub>GS</sub> = 20 V, I <sub>D</sub> = 4 A, T <sub>J</sub> = 150 °C	-	383	479	
		V <sub>GS</sub> = 18 V, I <sub>D</sub> = 4 A	-	280	350	
		V <sub>GS</sub> = 18 V, I <sub>D</sub> = 4 A, T <sub>J</sub> = 150 °C	-	400	500	
Dynamic						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 800 V, f = 1 MHz	-	447	-	pF
Output capacitance	C <sub>OSS</sub>		-	21.2	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	3.2	-	
Cross stored energy	E <sub>OSS</sub>		-	8.7	-	
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 18 V, I <sub>D</sub> = 4 A, V <sub>DS</sub> = 800 V	-	20.3	-	nC
Gate-source charge	Q <sub>gs</sub>		-	5.5	-	
Gate-drain charge	Q <sub>gd</sub>		-	7.9	-	
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> = 0 V, f = 1 MHz	-	34	-	Ω
Switching Characteristics						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -5 V ~ 18 V, I <sub>D</sub> = 4 A, V <sub>DS</sub> = 800 V, R <sub>g(ext)</sub> = 4.4 Ω	-	10	-	ns
Rise time	t <sub>r</sub>		-	11.5	-	
Turn-off delay time	t <sub>d(off)</sub>		-	9.5	-	
Fall time	t <sub>f</sub>		-	15	-	
Turn-on switching energy	E <sub>on</sub>		-	76	-	μJ
Turn-off switching energy	E <sub>off</sub>		-	5	-	
Body Diode Ratings and Characteristic						
Forward diode voltage	V <sub>SD</sub>	V <sub>GS</sub> = -5 V, I <sub>SD</sub> = 2 A, T <sub>J</sub> = 25 °C	-	4.6	-	V
Continuous diode forward current	I <sub>SD</sub>	V <sub>GS</sub> = -5 V, T <sub>J</sub> = 25 °C	-	-	7	A
Pulsed diode forward current	I <sub>SDM</sub>		-	-	21	
Reverse recovery time	t <sub>rr</sub>	V <sub>GS</sub> = -5 V, I <sub>SD</sub> = 4 A, V <sub>R</sub> = 800 V di/dt = 1000 A/μs	-	7.5	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	12	-	nC
Reverse recovery current	I <sub>rrm</sub>		-	2.8	-	A

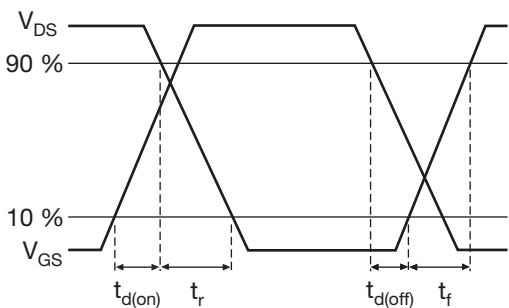
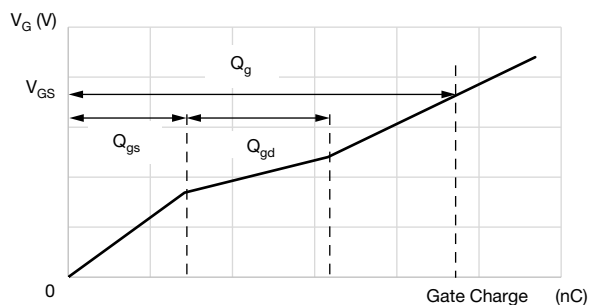
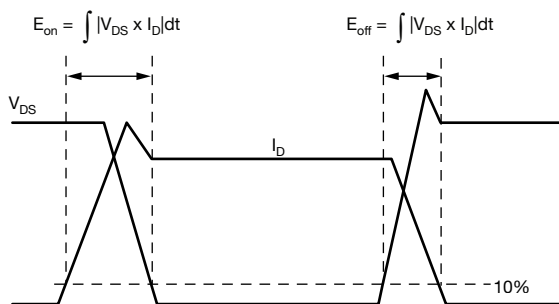
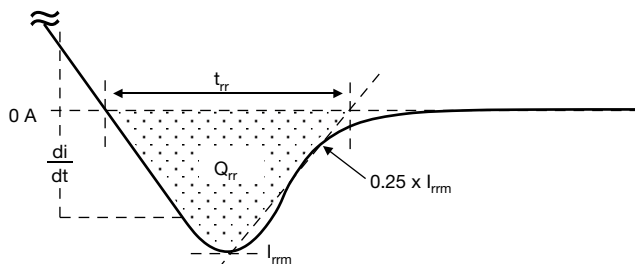
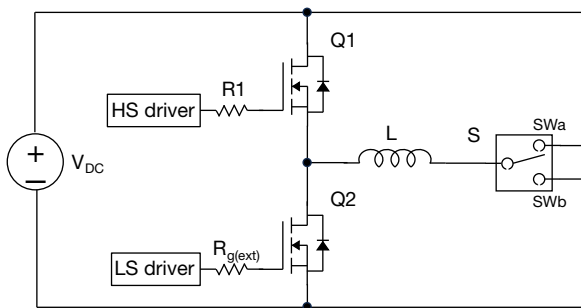
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Forward Transconductance vs. Drain Current**

**Fig. 3 - Typical Output Characteristics**

**Fig. 6 - Normalized On-Resistance vs. Drain Current**


**Fig. 7 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 10 - Drain-to-Source Voltage vs. Temperature**

**Fig. 8 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 11 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Normalized On-Resistance vs. Temperature**

**Fig. 12 - On-Resistance vs. Gate-to-Source Voltage**


**Fig. 13 - Threshold Voltage vs. Case Temperature**

**Fig. 15 - Output Capacitance and its Stored Energy vs. Drain-to-Source Voltage**

**Fig. 14 - Drain Current vs. Case Temperature**

**Fig. 16 - Power, Dissipated  $P_D$  vs. Case Temperature**

**Fig. 17 - Safe Operating Area**



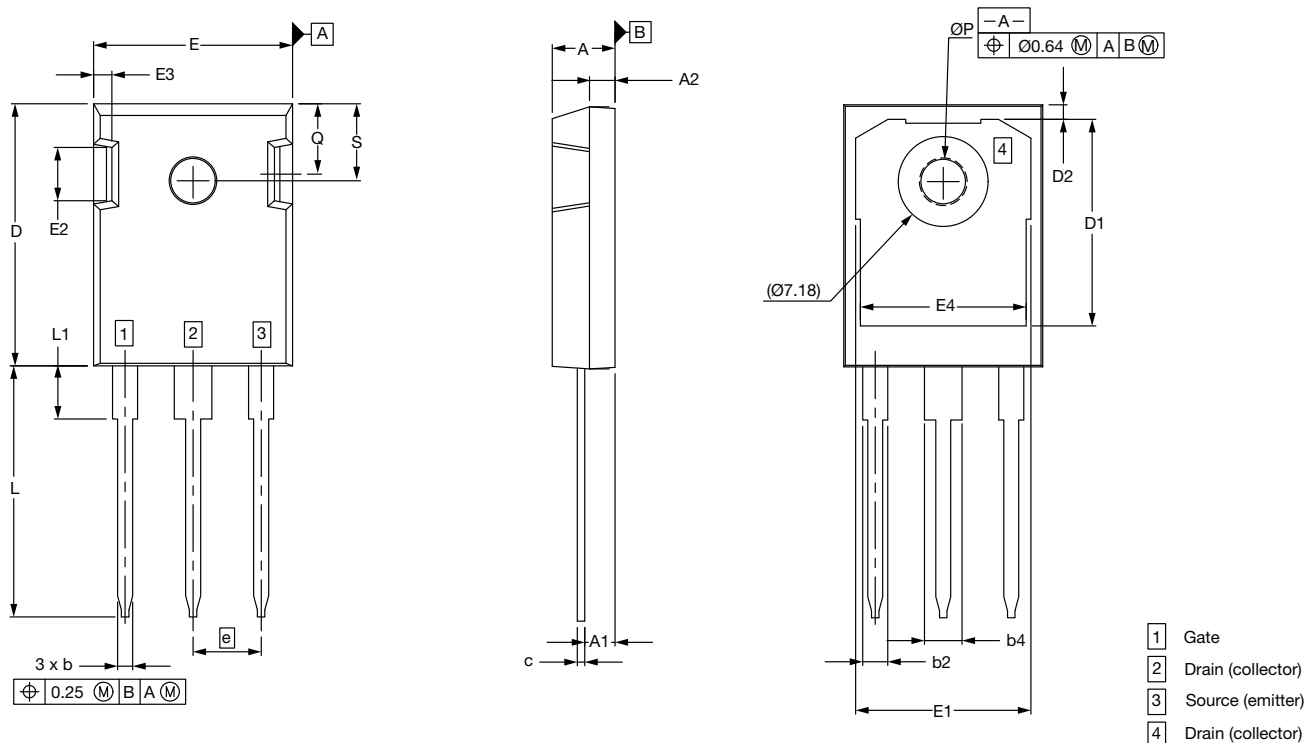
**Fig. 18 - Normalized Effective Transient Thermal Impedance**


**Fig. 19 - Waveforms of Switching Time**

**Fig. 22 - Waveforms for Gate Charge**

**Fig. 20 - Waveforms for Switching Energy**

**Fig. 23 - Waveforms for Reverse Recovery**

**Fig. 21 - Switching and Reverse Diode Characteristics Measurement Circuit**

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## Case Outline for TO-247AD 3L

**FACILITY CODE: N**


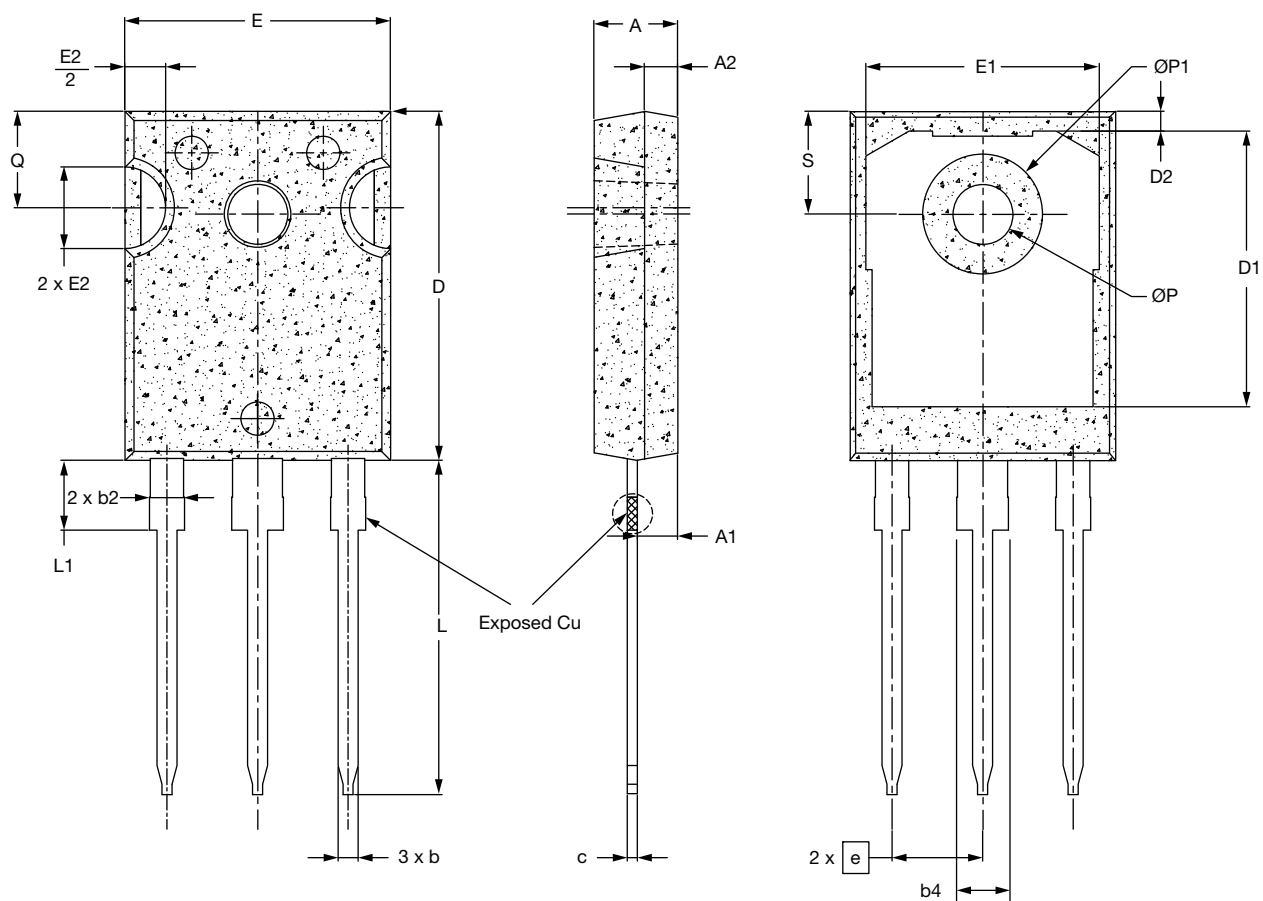
### Notes

- All metal surfaces: tin plated (MATTE), except area of cut
- Dimensioning and tolerancing confirm to ASME Y14.5M-1994
- All dimensions are in millimeters
- This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD
- Dimension b2 and b4 does not include dambar protrusion





**FACILITY CODE: 9**





DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.83	5.02	5.21
A1	2.29	2.41	2.55
A2	1.50	2.00	2.49
b	1.12	1.20	1.33
b2 <sup>(1)</sup>	1.91	2.00	2.39
b4 <sup>(1)</sup>	2.87	3.00	3.22
c	0.55	0.60	0.69
D <sup>(2)</sup>	20.80	20.95	21.10
D1 <sup>(3)</sup>	16.25	16.55	17.65
D2	0.51	1.19	1.35
E <sup>(2)</sup>	15.75	15.94	16.13
E1 <sup>(3)</sup>	13.46	14.02	14.16
E2	4.32	4.91	5.49
e	5.44 BSC.		
L	19.81	20.07	20.32
L1 <sup>(4)</sup>	4.10	4.19	4.40
ØP <sup>(5)</sup>	3.56	3.61	3.65
ØP1	7.19 ref.		
Q	5.39	5.79	6.20
S	6.04	6.17	6.30
ECN: E24-0303-Rev. B, 19-Aug-2024 DWG: 6118			

**Notes**

- Package reference: JEDEC TO-247, variation AD
  - All dimensions are in mm
  - Slot required, notch may be rounded
- <sup>(1)</sup> Dimension b2 and b4 does not include dambar protrusion  
<sup>(2)</sup> Dimension D and E do not include mold flash  
<sup>(3)</sup> Thermal pad contour optional within dimension D1 and E1  
<sup>(4)</sup> Lead Finish Uncontrolled In L1  
<sup>(5)</sup> ØP to have a draft angle of 1.5 ° ref. to the top of the part with hole diameter of 3.91mm



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